

In the Claims

Claims 1-62 (canceled).

Claim 63 (new): A semiconductor construction comprising:

a substrate;

a pair of wordlines supported by the substrate; the wordlines each comprising a gate dielectric, an electrically conductive material and an electrically insulating cap; the electrically insulative caps of the wordlines having uppermost surfaces;

a source/drain region within the substrate between the wordlines, the source/drain region being electrically isolated from one of the wordlines and being part of a transistor comprising a gate contained by the other of the wordlines;

an electrically conductive pedestal between the wordlines, over the source/drain region, and electrically connected with the source/drain region; the electrically conductive pedestal having an uppermost surface; the uppermost surface of the conductive pedestal and the uppermost surfaces of the electrically insulative caps of the wordlines together forming a planar platform extending across the wordlines and the electrically conductive pedestal;

a first capacitor electrode over the planar platform and having a planar surface of conductively-doped silicon;

a planar second capacitor electrode over the first capacitor electrode planar surface and comprising one or more materials selected from the group consisting of metals and metal compounds;

a planar first dielectric layer between the first and second capacitor electrodes, the first dielectric layer comprising aluminum oxide;

a planar second dielectric layer between the first and second capacitor electrodes, the second dielectric layer comprising a metal oxide other than aluminum oxide;

wherein the first dielectric layer is between the second dielectric layer and the conductively-doped silicon; and

wherein the metal oxide of the second dielectric layer is in physical contact with the second capacitor electrode.

Claim 64 (new): The semiconductor construction of claim 63 further comprising one or more additional dielectric layers between the first and second capacitor electrodes besides the first and second dielectric layers.

Claim 65 (new): The semiconductor construction of claim 63 wherein the first and second dielectric layers are the only dielectric layers between the first and second capacitor electrodes.

Claim 66 (new): The semiconductor construction of claim 65 wherein the first and second dielectric layers have a combined thickness of from about 25Å to about 150Å.

Claim 67 (new): The semiconductor construction of claim 66 wherein the first dielectric layer has a thickness of from about 5Å to about 60Å.

Claim 68 (new): The semiconductor construction of claim 66 wherein the second dielectric layer has a thickness of from about 20Å to about 90Å.

Claim 69 (new): The semiconductor construction of claim 65 wherein the first and second dielectric layers have a combined thickness of from about 25Å to about 80Å.

Claim 70 (new): The semiconductor construction of claim 69 wherein the first dielectric layer has a thickness of from about 5Å to about 20Å.

Claim 71 (new): The semiconductor construction of claim 69 wherein the second dielectric layer has a thickness of from about 20Å to about 60Å.

Claim 72 (new): The semiconductor construction of claim 63 wherein the metal oxide of the second dielectric layer is selected from the group consisting of hafnium oxide, tantalum oxide and zirconium oxide.

Claim 73 (new): The semiconductor construction of claim 72 wherein the second dielectric layer consists essentially of hafnium oxide.

Claim 74 (new): The semiconductor construction of claim 72 wherein the second dielectric layer consists of hafnium oxide.

Claim 75 (new): The semiconductor construction of claim 72 wherein the second dielectric layer consists essentially of tantalum oxide.

Claim 76 (new): The semiconductor construction of claim 72 wherein the second dielectric layer consists of tantalum oxide.

Claim 77 (new): The semiconductor construction of claim 72 wherein the second dielectric layer consists essentially of zirconium oxide.

Claim 78 (new): The semiconductor construction of claim 72 wherein the second dielectric layer consists of zirconium oxide.

Claim 79 (new): The semiconductor construction of claim 63 wherein the aluminum oxide of the first dielectric layer is physically against the conductively-doped silicon of the first capacitor electrode.

Claim 80 (new): The semiconductor construction of claim 63 wherein:

- the first dielectric layer consists of aluminum oxide;
- the first dielectric layer has a pair of opposing surfaces;
- one of the opposing surfaces of the first dielectric layer is physically against the conductively-doped silicon surface of the first capacitor electrode; and
- the other of the opposing surfaces of the first dielectric layer is physically against the metal oxide of the second dielectric layer.

Claim 81 (new): The semiconductor construction of claim 80 wherein the first dielectric layer has a thickness between the opposing surfaces of from about 5Å to about 20Å.

Claim 82 (new): The semiconductor construction of claim 80 wherein the second dielectric layer consists of hafnium oxide.

Claim 83 (new): The semiconductor construction of claim 80 wherein the second dielectric layer consists of tantalum oxide.

Claim 84 (new): The semiconductor construction of claim 80 wherein the second dielectric layer consists of zirconium oxide.